

# SI2306

Rev.E Mar.-2016

## 描述 / Descriptions

SOT-23 塑封封装 N 道 MOS 场效应管。N- CHANNEL MOSFET in a SOT-23 Plastic Package.

## 特征 / Features

沟道场效应管,功率 MOS 晶体管。

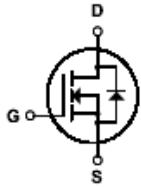
Trench FET Power MOSFET 100% Rg Tested.

## 用途 / Applications

主要用于显示屏驱动。

Primarily the display screen drive applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : S

PIN 2 : G

PIN 3 : D

## 印章代码 / Marking

Marking	H306
---------	------

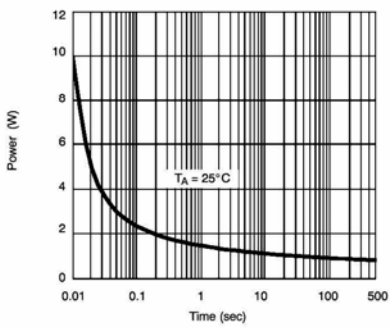
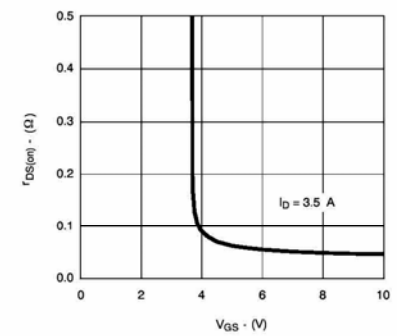
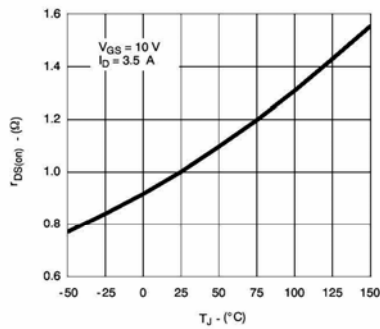
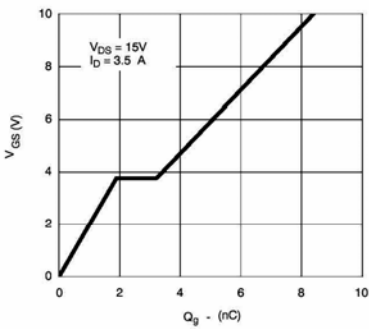
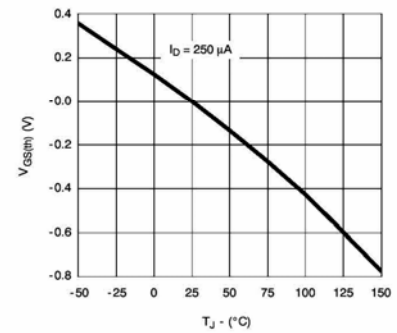
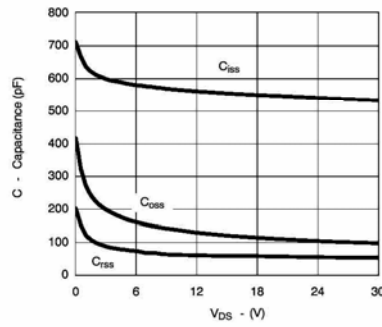
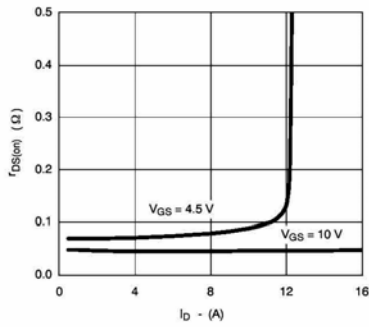
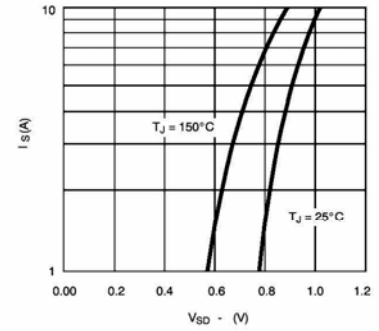
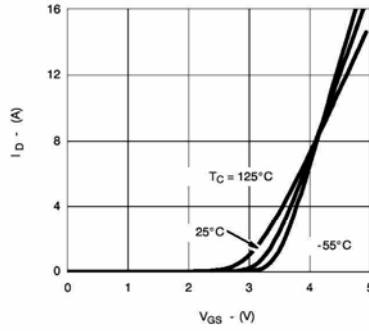
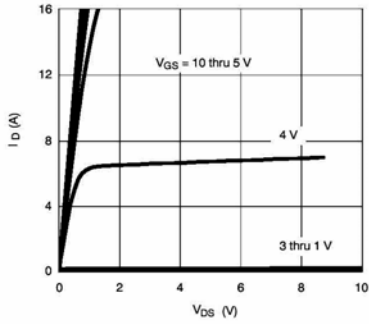
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±15	V
Drain Current – Continuous	$I_D$	3.5	A
Drain Current – Continuous	$I_D(T_A=70^\circ\text{C})$	2.8	A
Pulsed Drain Current	$I_{DM}$	16	A
Continuous Source Current	$I_S$	1.25	A
Power Dissipation	$P_D$	1.25	W
Power Dissipation	$P_D(T_A=70^\circ\text{C})$	0.80	W
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	0.8			V
Static Drain–Source On–Resistance	$R_{DS(on)1}$	$V_{GS}=10V$ $I_D=3.5A$		0.046	0.057	$\Omega$
	$R_{DS(on)2}$	$V_{GS}=4.5V$ $I_D=2.8A$		0.070	0.094	$\Omega$
Zero Gate Voltage Drain Current	$I_{DSS(1)}$	$V_{DS}=30V$ $V_{GS}=0V$			0.5	$\mu A$
	$I_{DSS(2)}$	$V_{DS}=30V$ $V_{GS}=0V$ $T_j=55^\circ\text{C}$			10	$\mu A$
Gate–Body Leakage.	$I_{GSS}$	$V_{GS}=\pm 15V$ $V_{DS}=0V$			±0.1	$\mu A$
State Drain Current	$I_{D(1)}$	$V_{DS}\geq 4.5V$ $V_{GS}=10V$	6.0			A
	$I_{D(2)}$	$V_{DS}\geq 4.5V$ $V_{GS}=4.5V$	4.0			A
Drain–Source Diode Forward Voltage	$V_{SD}$	$I_S=1.25A$ $V_{GS}=0V$		0.8	1.2	V
Forward Transconductance	$g_{FS}$	$V_{DS}=4.5V$ $I_D=3.5A$		6.9		S
Gate Resistance	$R_g$		0.5		2.4	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		555		pF
Output Capacitance	$C_{oss}$			120		
Reverse Transfer Capacitance	$C_{rss}$			60		
Turn–On Delay Time	$t_{d(on)}$	$V_{DD}=15V$ $R_L=15\Omega$ $I_D\approx 1.0A$ $V_{GEN}=10V$ $R_G=6.0\Omega$		9.0	20	ns
Turn–On Rise Time	$t_r$			7.5	18	
Turn–Off Delay Time	$t_{d(off)}$			17	35	
Turn–Off Fall Time	$t_f$			5.2	12	

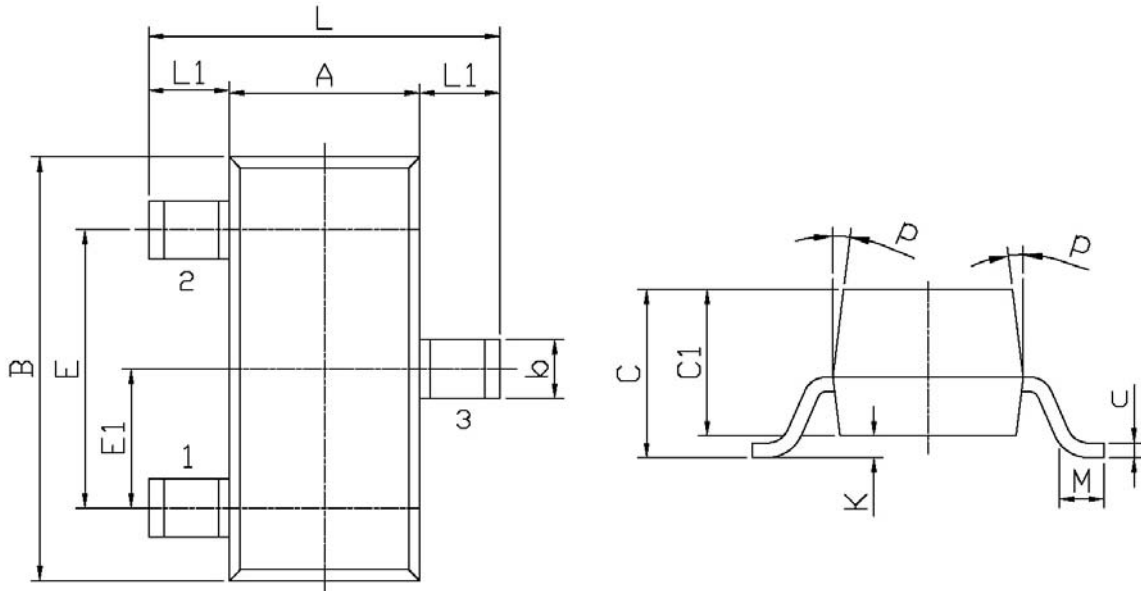
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

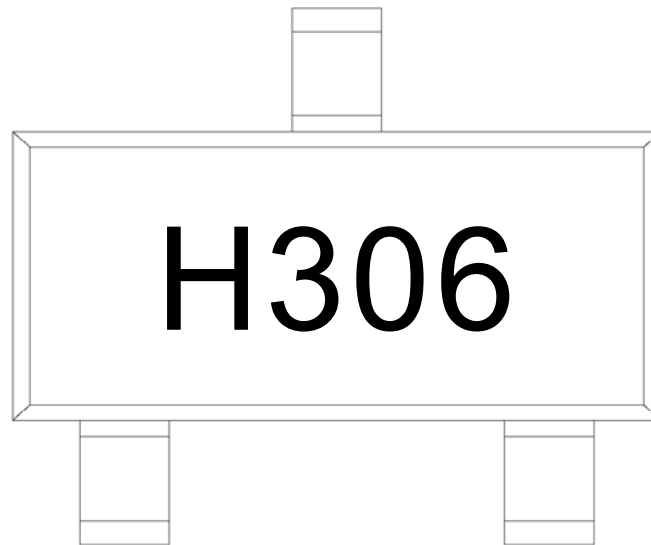
SOT-23

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20MIN	
E1	0.85	1.05	P	7°	
b	0.35	0.55			

印章说明 / Marking Instructions



说明：

H: 为公司代码

306: 为型号代码

Note:

H: Company Code.

306 : Product Type

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	8	240,000	7" ×8	180×120×180	385×257×392

**使用说明 / Notices**